

General Description

The WSP4800 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charges for most of the synchronous buck converter applications .

The WSP4800 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

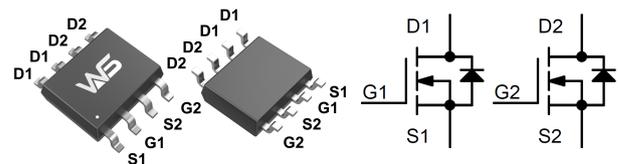
Product Summary

BVDSS	RDSON	ID
40V	32mΩ	6.0A

Application

- Power Management in Note book.
- Battery Powered System.
- Industrial DC/DC Conversion Circuits

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	6.0	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.4	A
I_{DM}	Pulsed Drain Current ^a	28	A
$P_D@T_A=25^\circ C$	Total Power Dissipation $T_A=25^\circ C$	1.5	W
$P_D@T_A=70^\circ C$	Total Power Dissipation $T_A=70^\circ C$	1.28	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ^b	---	110	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	62.5	$^\circ C/W$

Note a : Pulse width limited by max. junction temperature.

Note b : Surface Mounted on 1in² pad area, t =999sec.

Note c : UIS tested and pulse width limited by maximum junction temperature 150 $^\circ C$ (initial temperature $T_J=25^\circ C$).

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

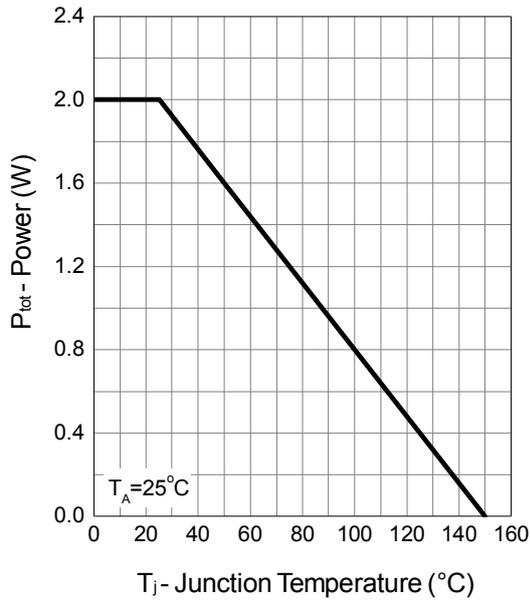
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}^c$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=6.0A$	---	32	35	m Ω
		$V_{GS}=4.5V, I_D=5.0A$	---	36	40	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	30	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Q_g^d	Total Gate Charge (4.5V)	$V_{DS}=20V, V_{GS}=4.5V, I_D=6A$	---	7.5	---	nC
Q_{gs}	Gate-Source Charge		---	3.24	---	
Q_{gd}	Gate-Drain Charge		---	2.75	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V, V_{GEN}=10V, R_G=6\Omega$ $I_D=1A, R_L=20\Omega.$	---	7.8	---	ns
T_r	Rise Time		---	6.9	---	
$T_{d(off)}$	Turn-Off Delay Time		---	22.4	---	
T_f	Fall Time		---	4.8	---	
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$	---	815	---	μF
C_{oss}	Output Capacitance		---	95	---	
C_{rss}	Reverse Transfer Capacitance		---	60	---	

Note c : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

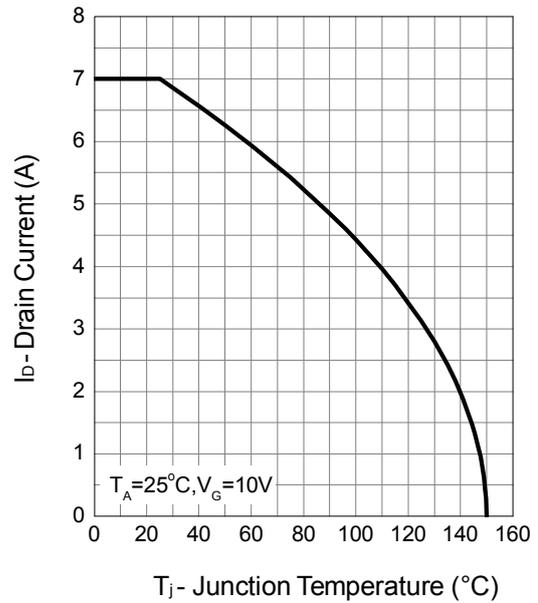
Note d : Guaranteed by design, not subject to production testing.

Typical Characteristics

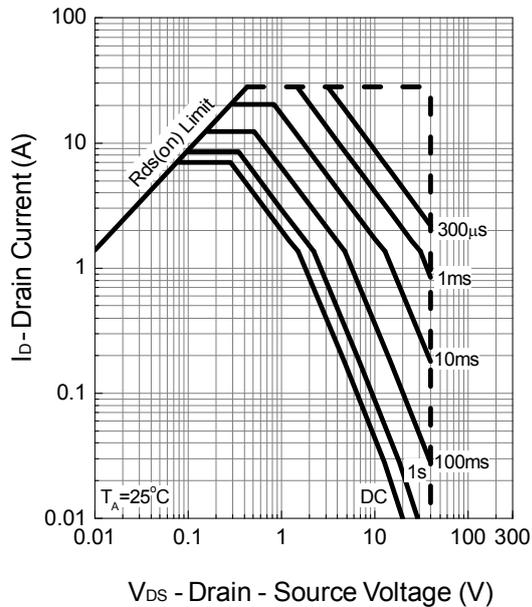
Power Dissipation



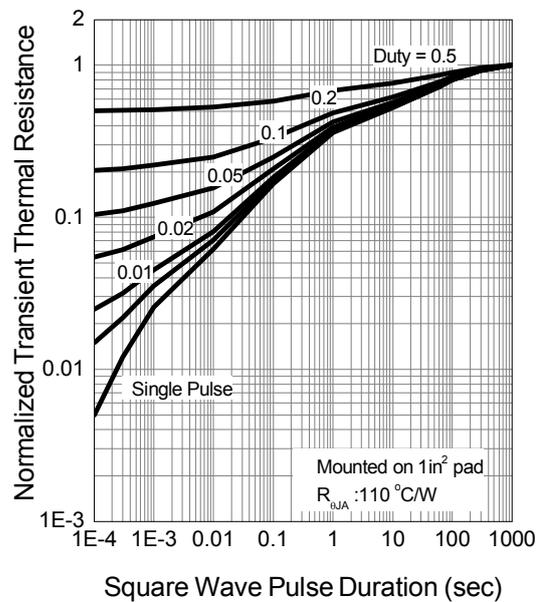
Drain Current



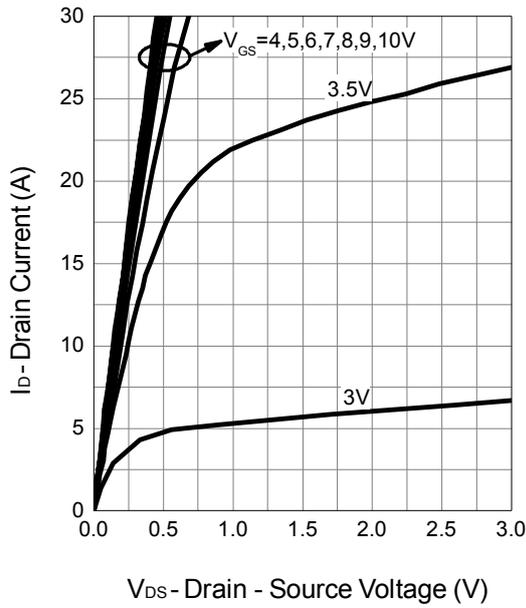
Safe Operation Area



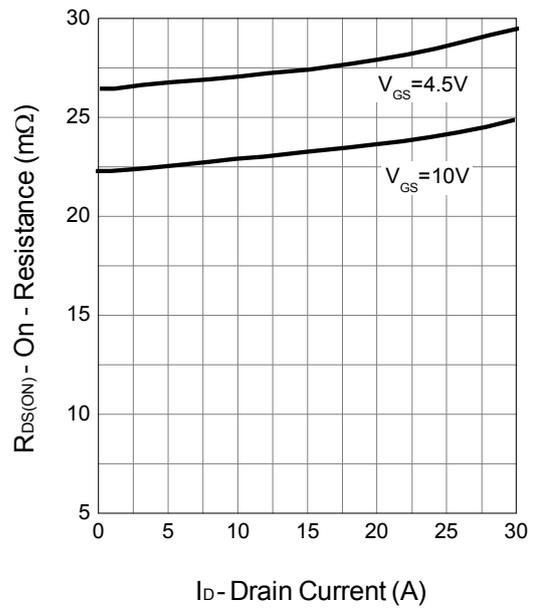
Thermal Transient Impedance



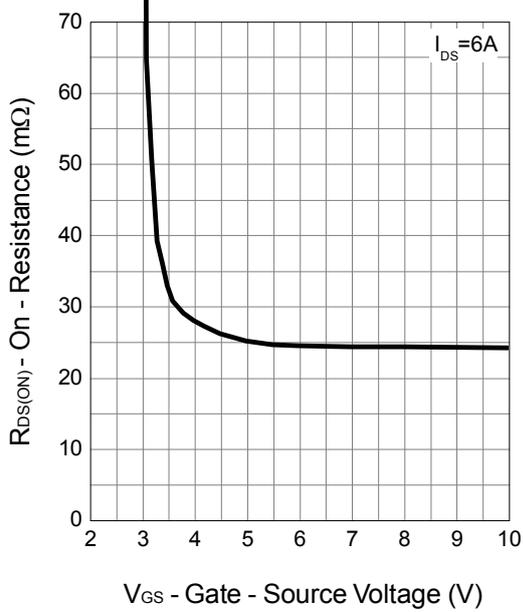
Output Characteristics



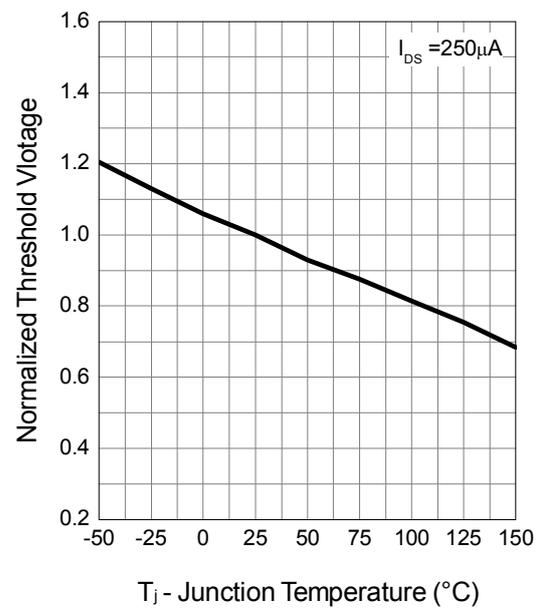
Drain-Source On Resistance



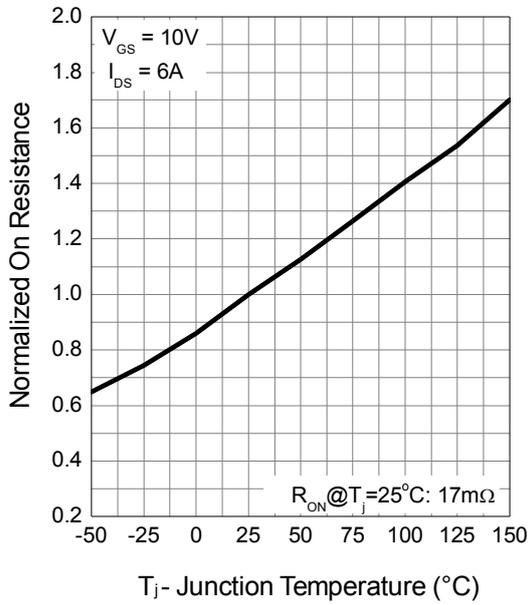
Gate-Source On Resistance



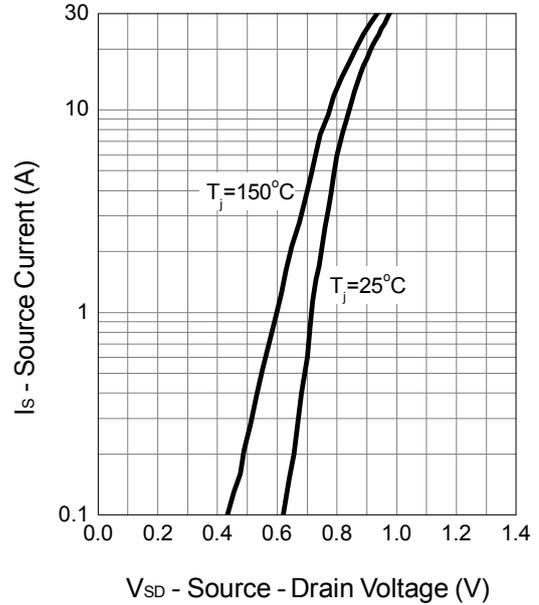
Gate Threshold Voltage



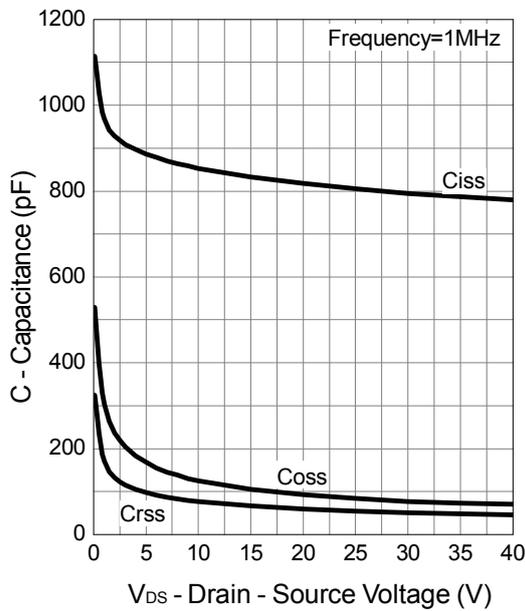
Drain-Source On Resistance



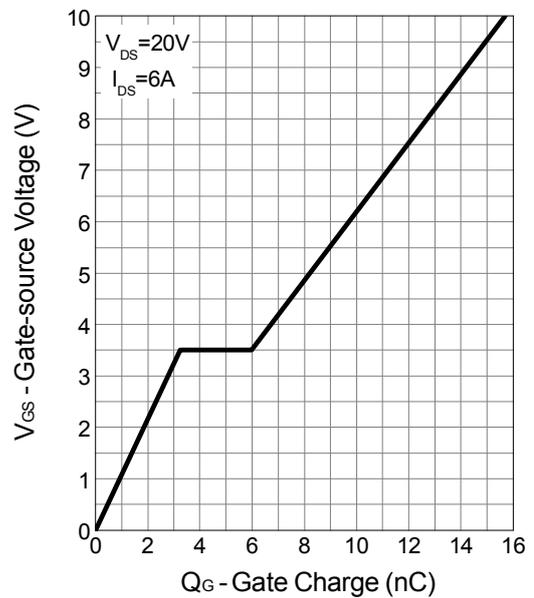
Source-Drain Diode Forward



Capacitance



Gate Charge





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